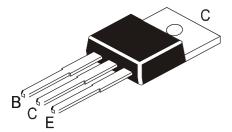


NPN PLASTIC POWER TRANSISTORS



MJE13004 MJE13005

TO-220 Plastic Package

Switchmode Series NPN Silicon Power Transistors

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	MJE13004	MJE13005	UNIT
Collector Emitter Sustaining Voltage	V _{CEO (sus)}	300	400	V
Collector Emitter Voltage	V _{CEV}	600	700	V
Emitter Base Voltage	V _{EBO}		9	V
Collector Current Continuous	I _C		4	A
*Peak	I _{CM}		8	A
Base Current Continuous	I _B		2	A
*Peak	I _{BM}		4	Α
Emitter Current Continuous	Ι _Ε		6	A
*Peak	I _{EM}		12	Α
Power Dissipation upto T _{a=} 25 ^o C	PD		2	W
Derate above=25°C			16	mW/ºC
Power Dissipation upto T _c =25°C	P _D		75	W
Derate above=25°C			600	mW/ºC
Operating And Storage Junction Temperature Range	T _{j,} T _{stg}		- 65 to +150	°C

* Pulse Test: Pulse Width =5ms, Duty Cycle<10%

THERMAL RESISTANCE

Junction to Case	R _{th (j-c)}	1.67	°C/W
Junction to Ambient in free air	R _{th (j-a)}	62.5	°C/W
Maxmium Lead Temperature for Soldering Purpose 1/8" from Case for 5 Seconds	TL	275	°C

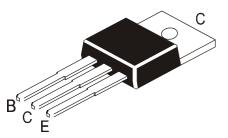
ELECTRICAL CHARACTERISTICS (T_c=25°C Unless Specified Otherwise)

DESCRIPTION	SYMBOL		MIN	TYP	MAX	UNIT
Collector Emitter sustaining voltage	**V _{CEO(sus)}	I _C =10mA, I _B =0				
		MJE13004	300			V
		MJE13005	400			V
Collector Cut off Current	I _{CEV}	V _{CEV} =Rated Value,V _{BE} =(off)=1.5V			1.0	mA
		T _C =100°C				
		V _{CEV} =Rated Value,V _{BE} =(off)=1.5V			5.0	mA
Emitter Cut off Current	I _{EBO}	$V_{EB}=9V, I_{C}=0$			1.0	mA
DC Current Gain	**h _{FE}	I _C =1A, V _{CE} =5V	10		60	
		I _C =2A, V _{CE} =5V	8		40	

**Pulse Test: Pulse Width=300ms, Duty Cycle<2%

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ELECTRICAL CHARACTERISTICS (T_c=25°C Unless Specified Otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Emitter Saturation Voltage	**V _{CE(sat)}	I _C =1A, I _B =0.2A			0.5	V
		I _C =2A, I _B =0.5A			0.6	V
		I _C =4A, I _B =1A			1.0	V
		I _C =2A, I _B =0.5A, T _c =100⁰C			1.0	V
Base Emitter Saturation Voltage	**V _{BE(sat)}	I _C =1A, I _B =0.2A			1.2	V
		I _C =2A, I _B =0.5A			1.6	V
		I _C =2A, I _B =0.5A, T _c =100°C			1.5	V
Current Gain-Bandwidth Product	f _T	I _C =500mA,V _{CE} =10V, f=1MHz	4			MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz		65		pF

SWITCHING CHARACTERISTICS

Resistive Load	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Delay Time	t _d				0.1	μs
Rise Time	t _r	V_{CC} =125V, I_{C} =2A, I_{B1} = I_{B2} =0.4A,			0.7	μs
Storage Time	t _s	t _p =25μs, Duty Cycle <u><</u> 1%			4.0	μs
Fall Time	t _f				0.9	μs

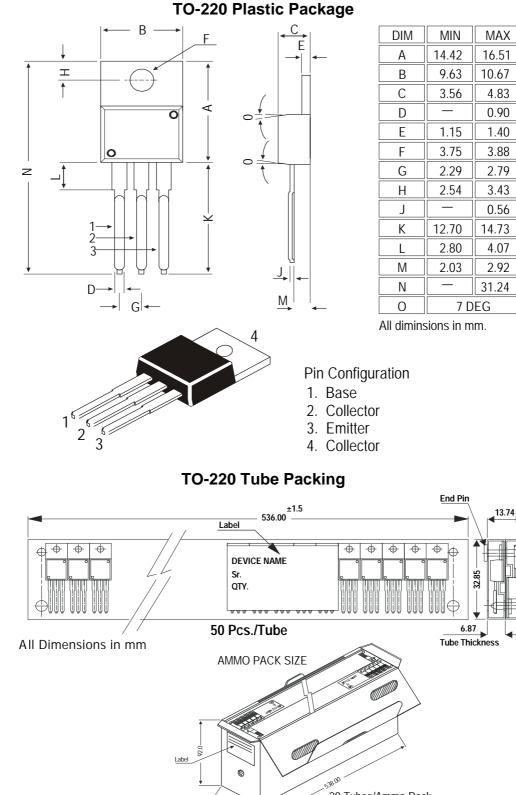
Inductive Load, Clamped

Voltage Storage Time	t _{sv}	V _{Clamp} =300V, I _C =2A, I _{B1} =0.4A,		4.0	μs
Crossover Time	t _C			0.9	μs
Fall Time	t _{fi}	$V_{BE(off)}=5V, T_c=100°C$	0.16		μs

**Pulse Test: Pulse Width=300ms, Duty Cycle<2%

MJE13004 MJE13005

TO-220 Plastic Package



20 Tubes/Ammo Pack 1000 Pcs./Ammo Pack

Packing Detail

PACKAGE	STANDARDPACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size Oty (Gr Wt
TO-220 /FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1.0K	17" x 15" x 13.5"	16.0K	36 kgs
	50 pcs/tube	120 gm/50 pcs	3.5" x 3.7" x 21.5"	1.0K	19" x 19" x 19"	10.0K	29 kgs

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TO-220 Plastic Package

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